

THE 67TH INTERNATIONAL



OPEN READINGS

CONFERENCE FOR STUDENTS OF PHYSICS AND NATURAL SCIENCES

**BOOK OF
ABSTRACTS** | **2024**



Vilnius
University

VILNIUS UNIVERSITY PRESS

Editors:

Martynas Keršys
Rimantas Naina
Vincentas Adomaitis
Emilijus Maskvytis

Cover and Interior Design:

Goda Grybauskaitė

Vilnius University Press
9 Saulėtekio Av., III Building, LT-10222 Vilnius
info@leidykla.vu.lt, www.leidykla.vu.lt/en/
www.knygynas.vu.lt, www.journals.vu.lt

Bibliographic information is available
on the Lithuanian Integral Library Information System (LIBIS) portal www.ibiblioteka.lt
ISBN 978-609-07-1051-7 (PDF)

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FEMTOSECOND ULTRAVIOLET LASER MODIFICATION OF GALLIUM NITRIDE THIN-FILM COATINGS

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Gallium nitride has recently stood out as a material that has a lot of useful properties for electronic and optoelectronic appliances, such as wide band-gap (3,4 eV), high heat capacity, thermal conductivity, break-down voltage, electron mobility and high quantum efficiencies [1]. These properties make gallium nitride a valuable material in developing light emitting diodes (LEDs) [2], field effect transistors (FETs) [3], high-temperature devices [4] and many others. To manufacture these devices from gallium nitride a high-quality processing is needed.

Recent advancements in the development of ultrashort pulse lasers allow high-quality micro-processing of materials. It is well known that the use of ultrashort laser pulses, compared to longer ones, give more control in the ablation process and also increase the resolution of micro-processing, due to reduction of heat-affected zones (HAZ) because the temporal length of the pulse is lower than the length of thermal diffusion. Most approaches use femtosecond lasers with wavelengths longer than ultraviolet [5]. However, shorter wavelengths in UV spectral range could benefit in decreasing heat-affected zones due to linear (one photon) absorption and smaller focus point, because it is directionally proportional to the wavelength. This technique was tested with the use of longer nanosecond pulses of excimer UV lasers [6]. Nevertheless, laser processing using UV femtosecond laser pulses has seldom been studied.

In this study we directly ablate thin-film undoped gallium nitride using femtosecond ultraviolet laser pulses [257 nm, 100 kHz, 240 fs] with different pulse energy and pulse overlapping. The topographies of ablated regions were measured with a profilometer (repeatability $\sigma_{n-1} = 12$ nm). The ablated structures were characterized using three variables: ablation depth, ablation efficiency and average modified surface roughness S_a , calculated according to ISO 25178-3:2012. Our results indicate that the use of femtosecond UV laser pulses enable high resolution and high-quality ablation with minimal heat affected zones (HAZ) while processing wide band-gap materials such as gallium nitride. We demonstrate the efficient ablation with average surface roughness S_a values in the frame of [16 nm - 86 nm] without any post-processing.

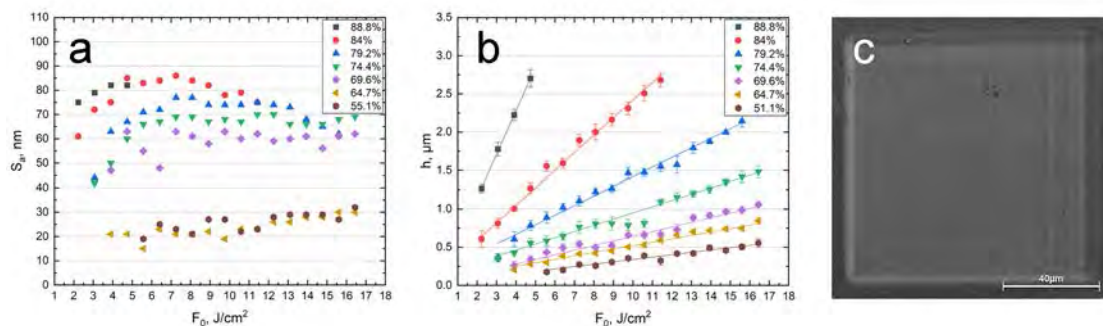


Fig. 1. Results of uGaN ablation using femtosecond UV pulses: (a) experimental data of average surface roughness of ablated areas as a function of pulse energy fluence, (b) experimental data of ablation depth as a function of pulse energy fluence, (c) SEM image of laser ablated area (PO = 79,2 %, $F_0 = 15,6$ J/cm², $S_a = 62$ nm).

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